TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7MA257FK

Low Voltage Quad 2-Channel Multiplexer with 3.6 V Tolerant Inputs and Outputs

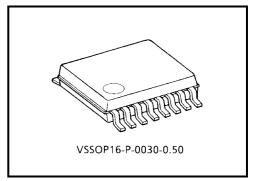
The TC7MA257FK is a high performance CMOS multiplexer. Designed for use in 1.8 , 2.5 or 3.3 V systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

It is also designed with over voltage tolerant inputs and outputs up to $3.6\ V\!.$

It consists of four 2-input digital multiplexers with common SELECT and $\overline{OUTPUTENABLE}$ (\overline{OE}).

If \overline{OE} is set high the outputs are held in a high-impedance state. The SELECT decoding determines whether the A or B inputs get routed to their corresponding Y outputs.

All inputs are equipped with protection circuits against static discharge.



Weight: 0.02 g (typ.)

Features

- Low voltage operation: $V_{CC} = 1.8 \sim 3.6 \text{ V}$
- High speed operation: $t_{pd} = 3.0 \text{ ns (max) (VCC} = 3.0 \sim 3.6 \text{ V)}$

 $t_{pd} = 4.0 \text{ ns (max) (VCC} = 2.3 \sim 2.7 \text{ V)}$

 $t_{pd} = 8.0 \text{ ns (max) (VCC} = 1.8 \text{ V)}$

- 3.6 V tolerant inputs and outputs.
- Output current: $I_{OH}/I_{OL} = \pm 24 \text{ mA (min)} (V_{CC} = 3.0 \text{ V})$

 $IOH/IOL = \pm 18 \text{ mA (min) (VCC} = 2.3 \text{ V)}$

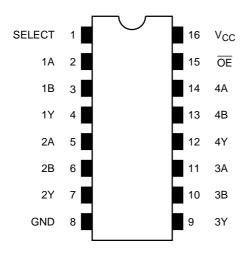
 $IOH/IOL = \pm 6 \text{ mA (min) (VCC} = 1.8 \text{ V)}$

- Latch-up performance: ±300 mA
- ESD performance: Machine model > ±200 V

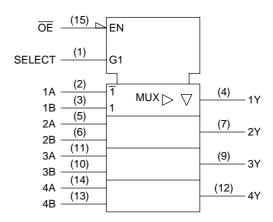
Human body model $> \pm 2000 \text{ V}$

- Package: VSSOP (US16)
- Power down protection is provided on all inputs and outputs.
- Supports live insertion/withdrawal (*)
 - *: To ensure the high-impedance state during power up or power down, $\overline{\text{OE}}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

Pin Assignment (top view)



IEC Logic Symbol



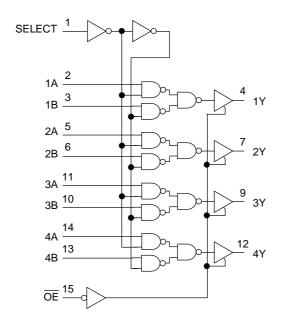
Truth Table

	Outputs			
ŌE	SELECT	А	В	Υ
Н	Х	Х	Х	Z
L	L	L	Х	L
L	L	Н	Х	Н
L	Н	Х	L	L
L	Н	Х	Н	Н

X: Don't care

Z: High impedance

System Diagram



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TC7MA257FK



Maximum Ratings

Characteristics	Symbol	Rating	Unit	
Power supply voltage	V _{CC}	-0.5~4.6	V	
DC input voltage	V _{IN}	-0.5~4.6	V	
		-0.5~4.6 (Note 1)		
DC output voltage	Vout	$-0.5 \sim V_{CC} + 0.5$ (Note 2)	V	
Input diode current	I _{IK}	-50	mA	
Output diode current	I _{OK}	±50 (Note 3)	mA	
DC output current	lout	±50	mA	
Power dissipation	P _D 180		mW	
DC V _{CC} /ground current	I _{CC} /I _{GND}	±100	mA	
Storage temperature	T _{stg}	-65~150	°C	

Note1: Off-state

Note2: High or low state. I_{OUT} absolute maximum rating must be observed.

Note3: $V_{OUT} < GND, V_{OUT} > V_{CC}$

Recommended Operating Range

Characteristics	Symbol	Rating	Unit	
Cumply voltage	\/	1.8~3.6	V	
Supply voltage	V _{CC}	1.2~3.6 (Note 4)	V	
Input voltage	V _{IN}	-0.3~3.6	V	
Output voltage	\/	0~3.6 (Note 5)	V	
Output voltage	Vout	0~V _{CC} (Note 6)	V	
		±24 (Note 7)		
Output current	I _{OH} /I _{OL}	±18 (Note 8)	mA	
		±6 (Note 9)		
Operating temperature	T _{opr}	-40~85	°C	
Input rise and fall time	dt/dv	0~10 (Note 10)	ns/V	

Note4: Data retention only

Note5: Off-state

Note6: High or low state

Note7: $V_{CC} = 3.0 \sim 3.6 \text{ V}$

Note8: $V_{CC} = 2.3 \sim 2.7 \text{ V}$

Note9: $V_{CC} = 1.8 \text{ V}$

Note10: $V_{IN} = 0.8 \sim 2.0 \text{ V}, V_{CC} = 3.0 \text{ V}$

Electrical Characteristics

DC Characteristics (Ta = $-40 \sim 85$ °C, 2.7 V < V_{CC} \leq 3.6 V)

Characteris	stics	Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit
	High level	V _{IH}		_	2.7~3.6	2.0	_	.,
Input voltage	Low level	V _{IL}		_	2.7~3.6	_	0.8	V
				I _{OH} = -100 μA	2.7~3.6	V _{CC} - 0.2	_	
	High level	V _{OH}	$V_{IN} = V_{IH}$ or V_{IL}	I _{OH} = -12 mA	2.7	2.2	_	
				$I_{OH} = -18 \text{ mA}$	3.0	2.4	_	
Output voltage				$I_{OH} = -24 \text{ mA}$	3.0	2.2	_	V
Louis			$I_{OL} = 100 \mu A$	2.7~3.6	_	0.2		
	Low level	Vol	$V_{IN} = V_{IH}$ or V_{IL}	I _{OL} = 12 mA	2.7	_	0.4	
	Low level	NOL		$I_{OL} = 18 \text{ mA}$	3.0	_	0.4	
				I _{OL} = 24 mA	3.0	_	0.55	
Input leakage currer	nt	I _{IN}	V _{IN} = 0~3.6 V		2.7~3.6	_	±5.0	μΑ
2 state output off sta	ato current	la-	$V_{IN} = V_{IH}$ or V_{IL}		2.7~3.6	_	±10.0	μА
3-state output off-state current		l _{OZ}	V _{OUT} = 0~3.6 V		2.7~3.0		±10.0	μА
Power off leakage c	urrent	I _{OFF}	V_{IN} , $V_{OUT} = 0 \sim 3.6 \text{ V}$		0	_	10.0	μΑ
Quiescent supply current		loo	V _{IN} = V _{CC} or GND		2.7~3.6	_	20.0	
Quiescent supply co	mem	Icc	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$		2.7~3.6	_	±20.0	μΑ
Increase in I _{CC} per i	nput	Δlcc	$V_{IH} = V_{CC} - 0.6 V$		2.7~3.6	_	750	

DC Characteristics (Ta = -40~85°C, 2.3 V \leq V_{CC} \leq 2.7 V)

Character	istics	Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit	
Input voltage	High level	V _{IH}		_	2.3~2.7	1.6	_	V	
input voitage	Low level	V _{IL}		_	2.3~2.7	_	0.7	V	
				$I_{OH} = -100 \mu A$	2.3~2.7	V _{CC} - 0.2	_		
	High level	Voн	V _{IN} = V _{IH} or V _{IL}	$I_{OH} = -6 \text{ mA}$	2.3	2.0	_		
				I _{OH} = -12 mA	2.3	1.8	_	٧	
Output voltage				I _{OH} = -18 mA	2.3	1.7	_		
			$V_{IN} = V_{IH}$ or V_{IL}	I _{OL} = 100 μA	2.3~2.7	_	0.2		
	Low level	V _{OL}		$V_{IN} = V_{IH} \text{ or } V_{IL}$	I _{OL} = 12 mA	2.3	_	0.4	
				I _{OL} = 18 mA	2.3	_	0.6		
Input leakage curre	ent	I _{IN}	V _{IN} = 0~3.6 V		2.3~2.7	_	±5.0	μΑ	
3-state output off-state current			$V_{IN} = V_{IH}$ or V_{IL}		$V_{IN} = V_{IH}$ or V_{IL}	2.3~2.7		±10.0	^
		loz	V _{OUT} = 0~3.6 V		2.3~2.1	_	±10.0	μА	
Power off leakage	current	loff	V _{IN} , V _{OUT} = 0~3.6 V		0		10.0	μΑ	
Quiescent supply of	current		V _{IN} = V _{CC} or GND		2.3~2.7	_	20.0	μА	
Quiescerit supply to	oun c ni	Icc	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$		2.3~2.7	_	±20.0	μΑ	

DC Characteristics (Ta = -40-85°C, 1.8 V \leq V_{CC} < 2.3 V)

Characteris	eristics Symbol Test Condition		V _{CC} (V)	Min	Max	Unit		
Input voltage	High level	V _{IH}		_		0.7 × V _{CC}	_	V
Input voltage	Low level	V _{IL}	-	_	1.8~2.3	_	0.2 × V _{CC}	V
	High level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	1.8	V _{CC} - 0.2	_	V
Output voltage				I _{OH} = -6 mA	1.8	1.4	_	
	Low level	V _{OL}	$V_{IN} = V_{IH}$ or V_{IL}	I _{OL} = 100 μA	1.8	_	0.2	
	Low level			I _{OL} = 6 mA	1.8	_	0.3	
Input leakage currer	nt	I _{IN}	V _{IN} = 0~3.6 V		1.8	_	±5.0	μΑ
3-state output off-state current		l _{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = 0 \sim 3.6 \text{ V}$		1.8		±10.0	μΑ
Power off leakage c	urrent	I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	_	10.0	μА
Quiescent supply cu	Ouissant summit summer		$V_{IN} = V_{CC}$ or GND		1.8		20.0	μА
Quiescent supply co	iii Giit	Icc	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$		1.8	_	±20.0	μΑ

AC Characteristics (Ta = -40~85°C, Input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF, $R_L = 500$ Ω)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Min	Max	Unit
Dranagation delay time	4		1.8	1.0	8.0	
Propagation delay time (A, B-Y)	t _{pLH}	Figure 1, Figure 2	2.5 ± 0.2	8.0	4.0	ns
(4, 5-1)	t _{pHL}		3.3 ± 0.3	0.6	3.0	
Drangation delay time	4		1.8	1.0	9.6	
Propagation delay time (SELECT-Y)	t _{pLH}	Figure 1, Figure 2	2.5 ± 0.2	0.8	4.8	ns
(SEEEGI-T)	t _{pHL}		3.3 ± 0.3	0.6	4.0	
	t _{pZL}	Figure 1, Figure 3	1.8	1.0	9.2	
3-state output enable time			2.5 ± 0.2	0.8	4.6	ns
			3.3 ± 0.3	0.6	3.5	
	t _{pLZ}		1.8	1.0	6.8	
3-state output disable time		Figure 1, Figure 3	2.5 ± 0.2	8.0	3.8	ns
			3.3 ± 0.3	0.6	3.5	
Output to output skew	.		1.8	_	0.5	
	t _{osLH}	(Note 11)	2.5 ± 0.2	_	0.5	ns
	t _{osHL}		3.3 ± 0.3	_	0.5	

For $C_L = 50 \ pF$, add approximately 300 ps to the AC maximum specification.

Note 11: This parameter is guaranteed by design. $(t_{OSLH} = |t_{PLHm} - t_{PLHn}|, \, t_{OSHL} = |t_{PHLm} - t_{PHLn}|)$

Dynamic Switching Characteristics (Ta = 25°C, Input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Тур.	Unit
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (Note 1)	2) 1.8	0.25	
Quiet output maximum dynamic V _{OL}	V _{OLP}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	2) 2.5	0.6	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (Note:	2) 3.3	0.8	
	V _{OLV}	$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	2) 1.8	-0.25	V
Quiet output minimum dynamic V _{OL}		$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (Note:	2) 2.5	-0.6	
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	2) 3.3	-0.8	
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	2) 1.8	1.5	
Quiet output minimum dynamic V _{OH}	V _{OHV}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	2) 2.5	1.9	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (Note:	2) 3.3	2.2	

Note 12: This parameter is guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

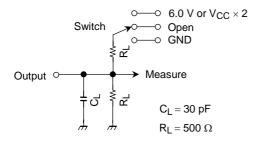
Characteristics	Cumbal	Test Condition			Tun	Unit
Characteristics	Symbol	rest Condition		V _{CC} (V)	Тур.	
Input capacitance	C _{IN}	_		1.8, 2.5, 3.3	6	pF
Output capacitance	CO	_		1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	C _{PD}	f _{IN} = 10 MHz (No	ote 13)	1.8, 2.5, 3.3	20	pF

Note 13: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$

AC Test Circuit



Parameter	Switch		
t _{pLH} , t _{pHL}	Open		
^t pLZ ^{, †} pZL	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$		
t _{pHZ} , t _{pZH}	GND		

Figure 1

AC Waveform

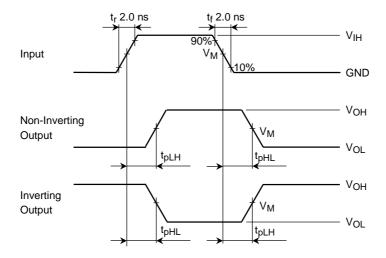


Figure 2 t_{pLH}, t_{pHL}

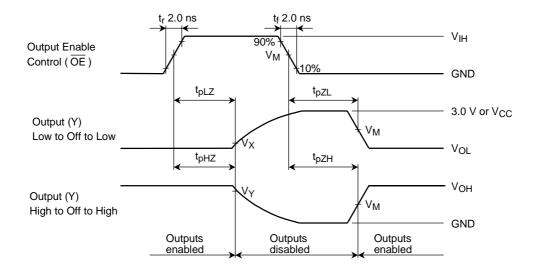
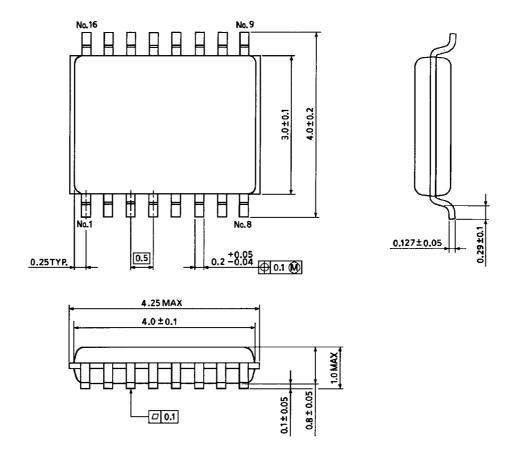


Figure 3 t_{pLZ} , t_{pHZ} , t_{pZL} , t_{pZH}

Symbol		V _{CC}	
Syllibol	$3.3\pm0.3~\textrm{V}$	$2.5\pm0.2\textrm{V}$	1.8 V
V _{IH}	2.7 V	V _{CC}	Vcc
V_{M}	1.5 V	V _{CC} /2	V _{CC} /2
V _X	V _{OL} + 0.3 V	V _{OL} + 0.15 V	V _{OL} + 0.15 V
VY	V _{OH} – 0.3 V	V _{OH} – 0.15 V	V _{OH} – 0.15 V

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Package Dimensions



Weight: 0.02 g (typ.)

2001-10-23

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